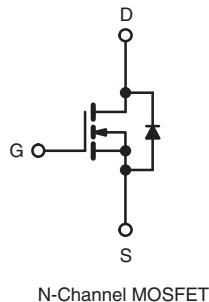


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.110
Q_g (Max.) (nC)	330	
Q_{gs} (nC)	84	
Q_{gd} (nC)	150	
Configuration	Single	


RoHS*
COMPLIANT

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Enhanced Body Diode dV/dt Capability
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Hard Switching Primary or PFC Switch
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Motor Drive

ORDERING INFORMATION

Package	Super-247		
Lead (Pb)-free	IRFPS40N60KPbF SiHFPS40N60K-E3		
SnPb	IRFPS40N60K SiHFPS40N60K		

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	40	A
		24	
Pulsed Drain Current ^a	I_{DM}	160	
Linear Derating Factor		4.5	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	600	mJ
Repetitive Avalanche Current ^a	I_{AR}	40	A
Repetitive Avalanche Energy ^a	E_{AR}	57	mJ
Maximum Power Dissipation	P_D	570	W
Peak Diode Recovery dV/dt ^c	dV/dt	7.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25$ °C, $L = 0.84$ mH, $R_g = 25$ Ω, $I_{AS} = 38$ A, dV/dt = 5.5 V/ns (see fig. 12a).
- $I_{SD} \leq 38$ A, $dI/dt \leq 150$ A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.22	

SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

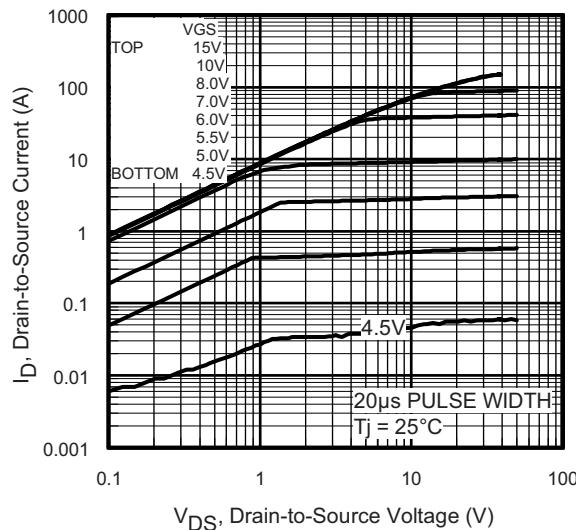
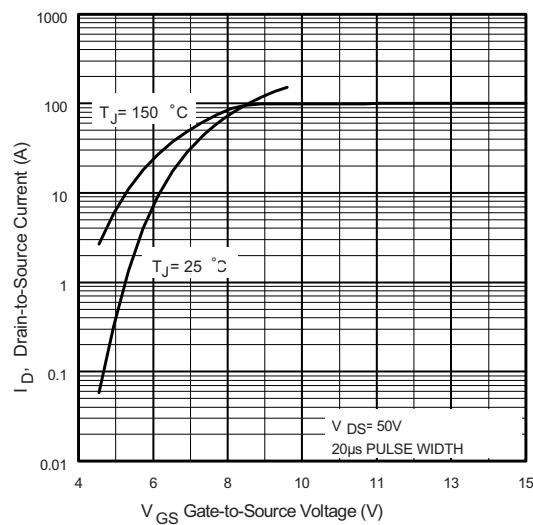
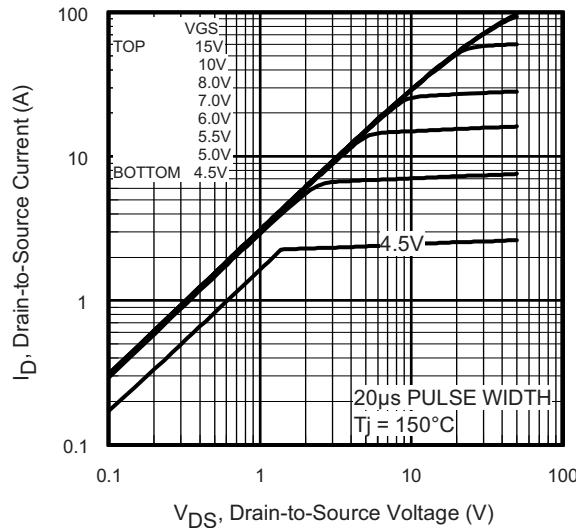
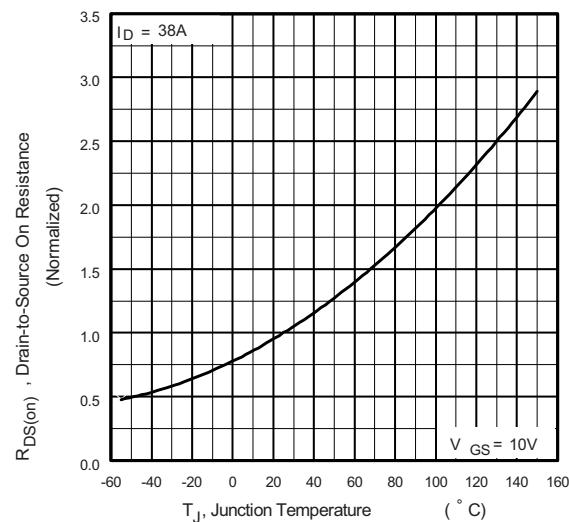
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$	$I_D = 250 \mu\text{A}$	600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1 \text{ mA}$		-	0.63	-	$^\circ\text{C}/\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		3.0	-	5.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30 \text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	50	μA
		$V_{DS} = 480 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 24 \text{ A}^b$	-	0.110	0.130	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50 \text{ V}$, $I_D = 24 \text{ A}^b$		21	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$, see fig. 5	$V_{GS} = 0 \text{ V}$	-	7970	-	pF
Output Capacitance	C_{oss}			-	750	-	
Reverse Transfer Capacitance	C_{rss}			-	75	-	
Output Capacitance	C_{oss}	$V_{DS} = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$	$V_{GS} = 0 \text{ V}$	-	9440	-	nC
				-	200	-	
Effective Output Capacitance	$C_{oss eff.}$	$V_{DS} = 0 \text{ V to } 480 \text{ V}^c$		-	260	-	ns
Total Gate Charge	Q_g	$I_D = 38 \text{ A}$, $V_{DS} = 480 \text{ V}$, see fig. 6 and 13 ^b	$V_{GS} = 10 \text{ V}$	-	-	330	
Gate-Source Charge	Q_{gs}			-	-	84	
Gate-Drain Charge	Q_{gd}			-	-	150	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300 \text{ V}$, $I_D = 38 \text{ A}$, $R_G = 4.3 \Omega$, see fig. 10 ^b	$V_{GS} = 10 \text{ V}$	-	47	-	
Rise Time	t_r			-	110	-	
Turn-Off Delay Time	$t_{d(off)}$			-	97	-	
Fall Time	t_f			-	60	-	

Drain-Source Body Diode Characteristics

Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	40	A	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	160		
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}$, $I_S = 38 \text{ A}$, $V_{GS} = 0 \text{ V}^b$		-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}$	$I_F = 38 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$	-	630	950	ns	
		$T_J = 125^\circ\text{C}$		-	730	1090		
Body Diode Reverse Recovery Charge	Q_{rr}	$T_J = 25^\circ\text{C}$		-	14	20	μC	
		$T_J = 125^\circ\text{C}$		-	17	25		
Body Diode Recovery Current	I_{RRM}	$T_J = 25^\circ\text{C}$		-	39	58	A	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)						

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300 \mu\text{s}$; duty cycle $\leq 2 \%$.
- c. $C_{oss eff.}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

IRFPS40N60K, SiHFPS40N60K

Vishay Siliconix

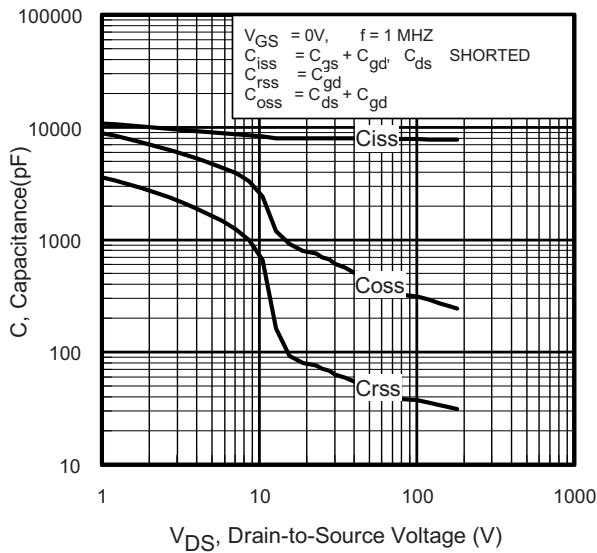


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

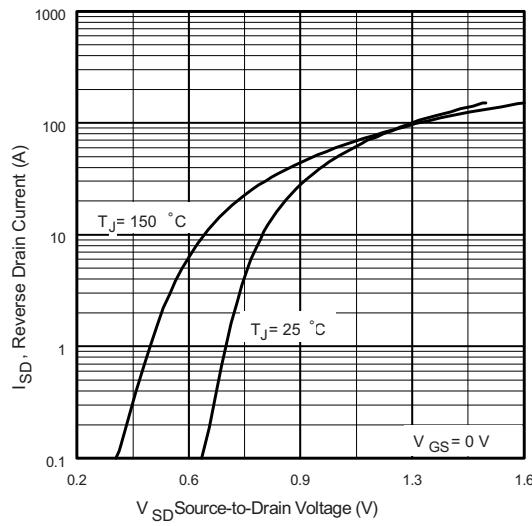


Fig. 7 - Typical Source-Drain Diode Forward Voltage

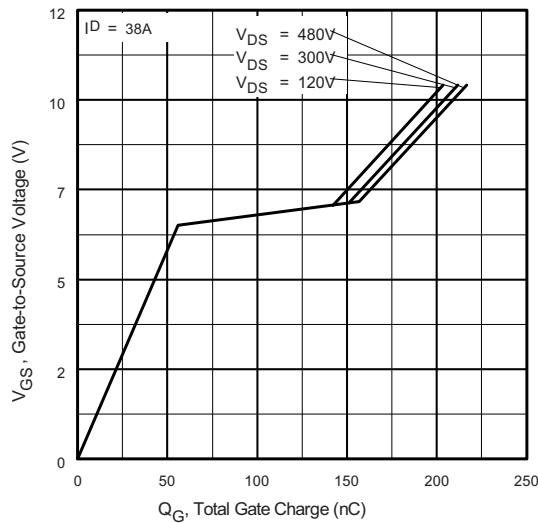


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

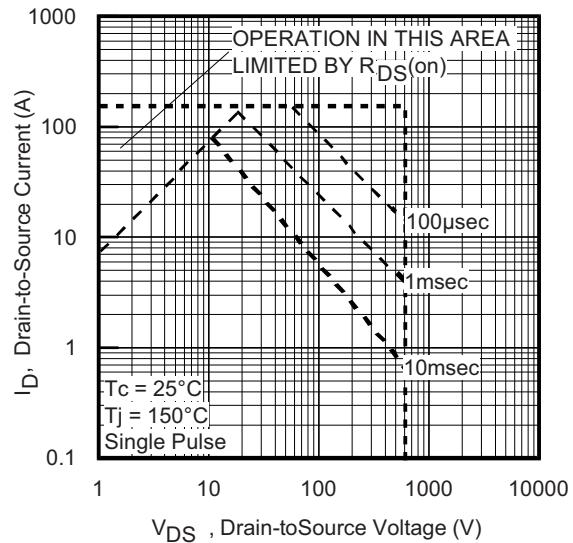


Fig. 8 - Maximum Safe Operating Area

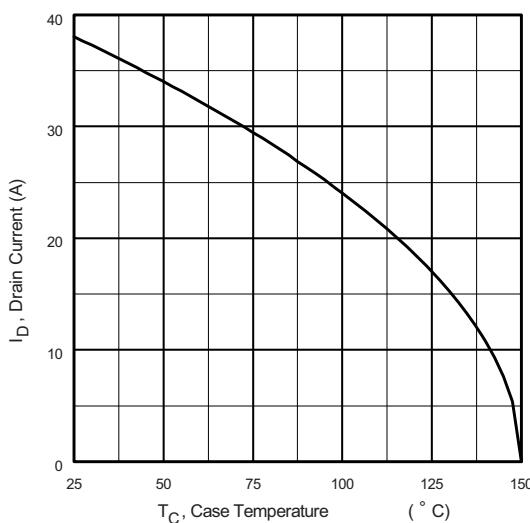


Fig. 9 - Maximum Drain Current vs. Case Temperature

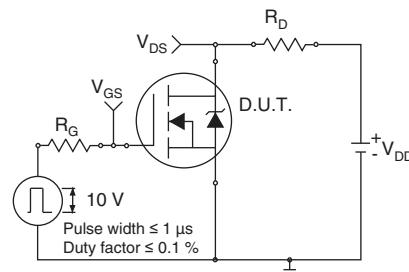


Fig. 10a - Switching Time Test Circuit

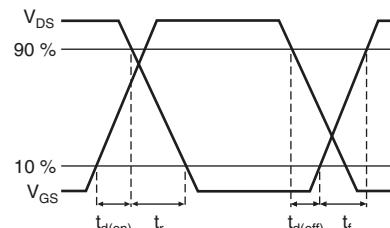


Fig. 10b - Switching Time Waveforms

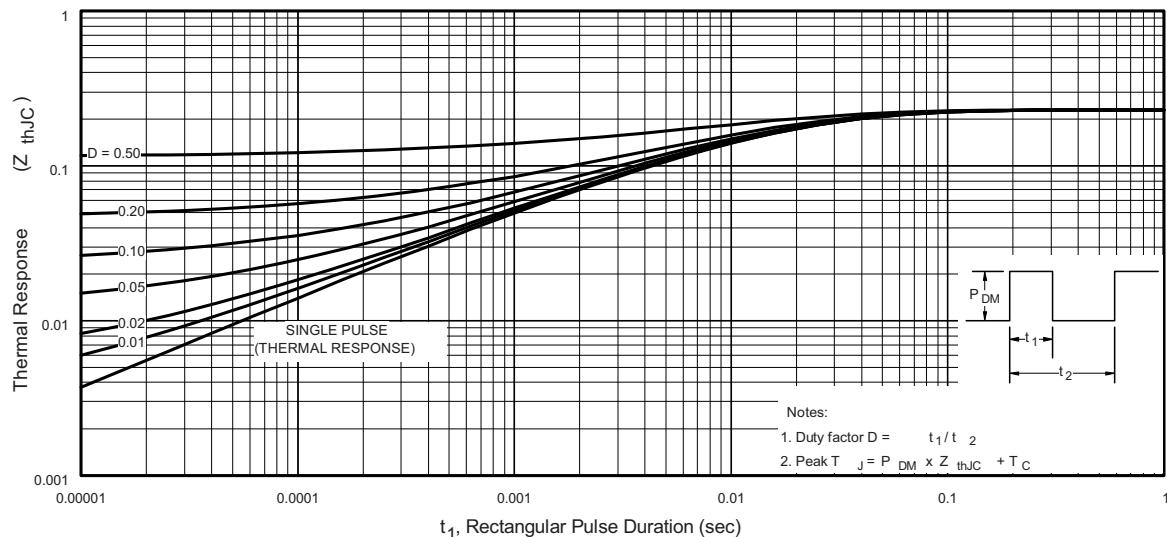


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRFPS40N60K, SiHFPS40N60K

Vishay Siliconix

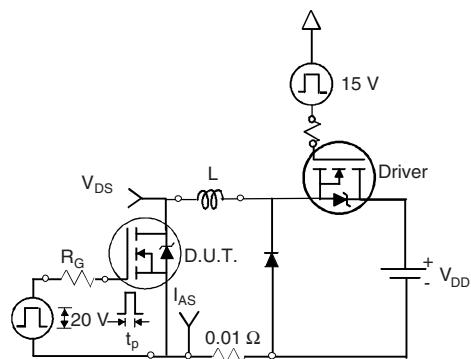


Fig. 12a - Unclamped Inductive Test Circuit

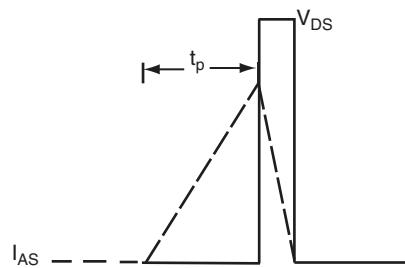


Fig. 12b - Unclamped Inductive Waveforms

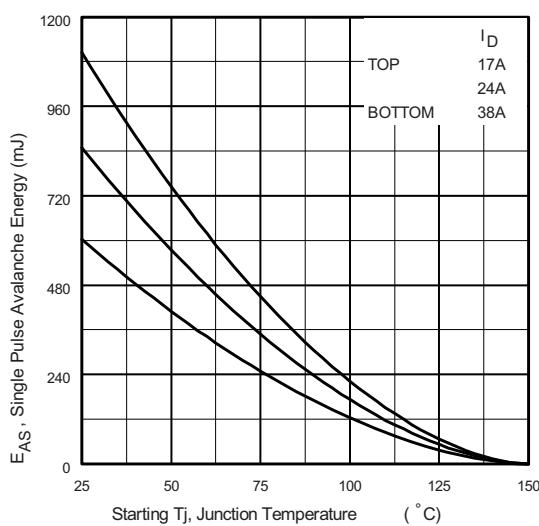


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

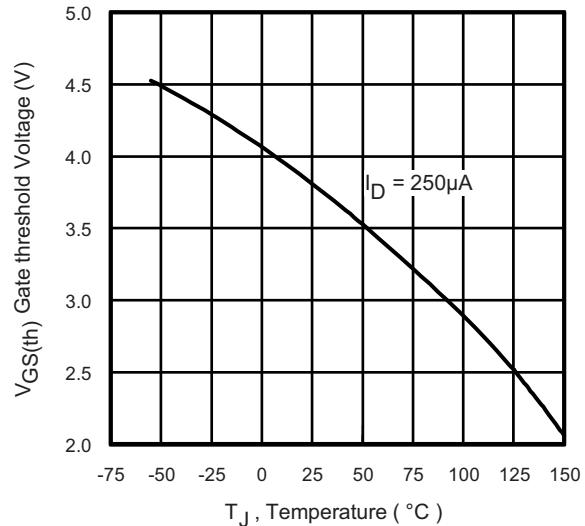


Fig. 12d - Threshold Voltage vs. Temperature

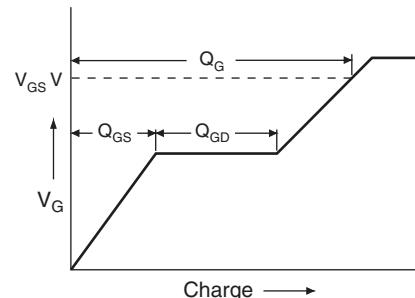


Fig. 13a - Basic Gate Charge Waveform

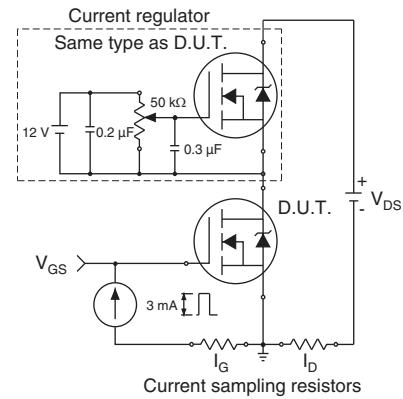
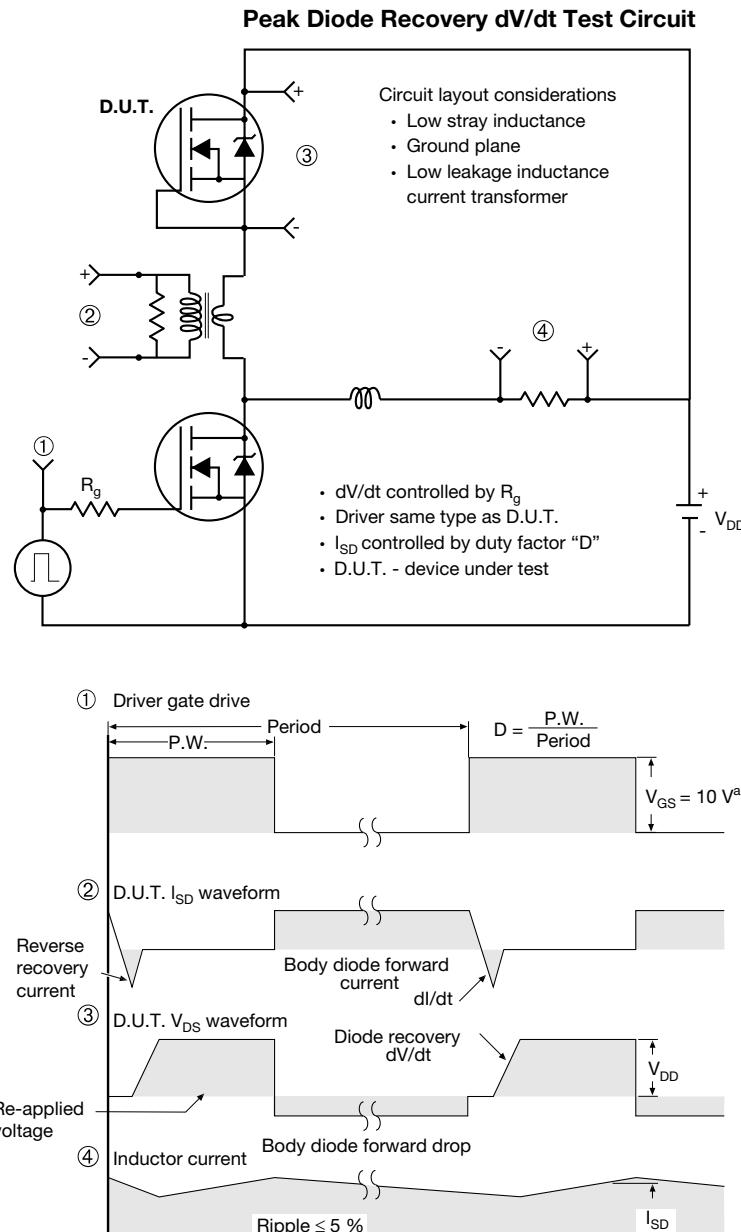
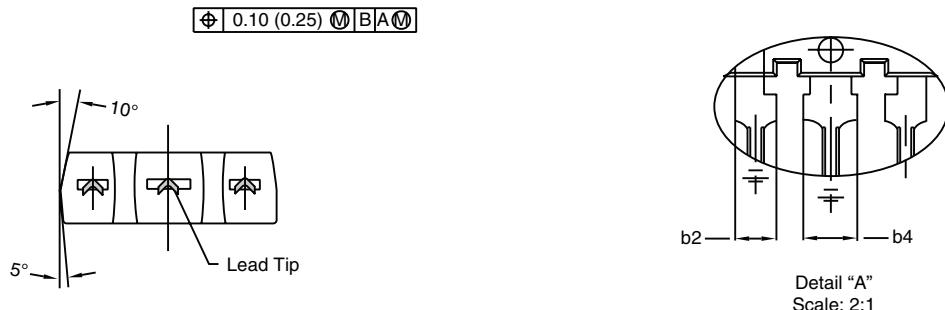
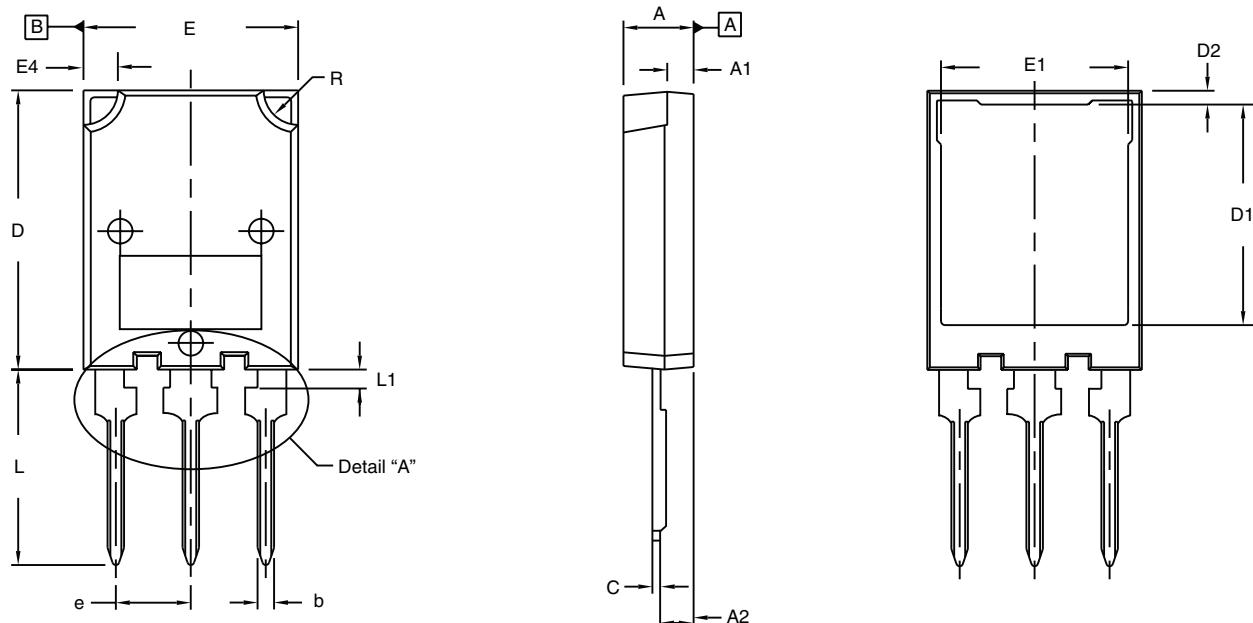


Fig. 13b - Gate Charge Test Circuit


Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91261.

TO-274AA (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c	0.80	1.20	0.031	0.047
D	19.80	20.80	0.780	0.819

ECN: S-82247-Rev. A, 06-Oct-08
DWG: 5975

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.70	1.30	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.00	1.60	0.039	0.063
R	2.00	3.00	0.079	0.118

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994.
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outer extremes of the plastic body.
- Outline conforms to JEDEC outline to TO-274AA.



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помошь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помошь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.